



# 10BQ100

## SCHOTTKY RECTIFIER

1 Amp

$$I_{F(AV)} = 1 \text{ Amp}$$
$$V_R = 100V$$

### Major Ratings and Characteristics

Characteristics	10BQ100	Units
$I_{F(AV)}$ Rectangular waveform	1.0	A
$V_{RRM}$	100	V
$I_{FSM}$ @tp = 5 $\mu$ s sine	780	A
$V_F$ @1.0 Apk, $T_J = 125^\circ\text{C}$	0.62	V
$T_J$ range	-55 to 175	$^\circ\text{C}$

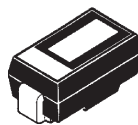
### Description/ Features

The 10BQ100 surface-mount Schottky rectifier has been designed for applications requiring low forward drop and very small foot prints on PC boards. Typical applications are in disk drives, switching power supplies, converters, free-wheeling diodes, battery charging, and reverse battery protection.

- Small foot print, surface mountable
- Low forward voltage drop
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability

### Case Styles

10BQ100



SMB





## 10BQ100

### Voltage Ratings

Part number	10BQ100
$V_R$ Max. DC Reverse Voltage (V)	100
$V_{RWM}$ Max. Working Peak Reverse Voltage (V)	

### Absolute Maximum Ratings

Parameters	10BQ	Units	Conditions
$I_{F(AV)}$ Max. Average Forward Current	1.0	A	50% duty cycle @ $T_L = 152^\circ\text{C}$ , rectangular wave form
$I_{FSM}$ Max. Peak One Cycle Non-Repetitive Surge Current	780	A	Following any rated load condition and with rated $V_{RRM}$ applied
	38		
$E_{AS}$ Non- Repetitive Avalanche Energy	1.0	mJ	$T_J = 25^\circ\text{C}$ , $I_{AS} = 0.5\text{A}$ , $L = 8\text{mH}$
$I_{AR}$ Repetitive Avalanche Current	0.5	A	Current decaying linearly to zero in 1 $\mu\text{sec}$ Frequency limited by $T_J$ max. $V_a = 1.5 \times V_r$ typical

### Electrical Specifications

Parameters	10BQ	Units	Conditions
$V_{FM}$ Max. Forward Voltage Drop (1) * See Fig. 1	0.78	V	@ 1A
	0.89	V	@ 2A
	0.62	V	@ 1A
	0.72	V	@ 2A
$I_{RM}$ Max. Reverse Leakage Current (1) * See Fig. 2	0.5	mA	$T_J = 25^\circ\text{C}$
	1	mA	$T_J = 125^\circ\text{C}$
$C_T$ Typical Junction Capacitance	42	pF	$V_R = 5V_{DC}$ , (test signal range 100kHz to 1MHz) $25^\circ\text{C}$
$L_S$ Typical Series Inductance	2.0	nH	Measured lead to lead 5mm from package body
$dv/dt$ Max. Volatge Rate of Charge (Rated $V_R$ )	10000	V/ $\mu\text{s}$	

(1) Pulse Width < 300 $\mu\text{s}$ , Duty Cycle < 2%

### Thermal-Mechanical Specifications

Parameters	10BQ	Units	Conditions
$T_J$ Max. Junction Temperature Range (*)	-55 to 175	$^\circ\text{C}$	
$T_{stg}$ Max. Storage Temperature Range	-55 to 175	$^\circ\text{C}$	
$R_{thJL}$ Max. Thermal Resistance Junction to Lead (**)	36	$^\circ\text{C}/\text{W}$	DC operation
$R_{thJA}$ Max. Thermal Resistance Junction to Ambient	80	$^\circ\text{C}/\text{W}$	
wt Approximate Weight	0.10(0.003)	g(oz.)	
Case Style	SMB		Similar DO-214AA
Device Marking	IR1J		

(\*)  $\frac{dP_{tot}}{dT_J} < \frac{1}{R_{th(j-a)}}$  thermal runaway condition for a diode on its own heatsink

(\*\*) Mounted 1 inch square PCB

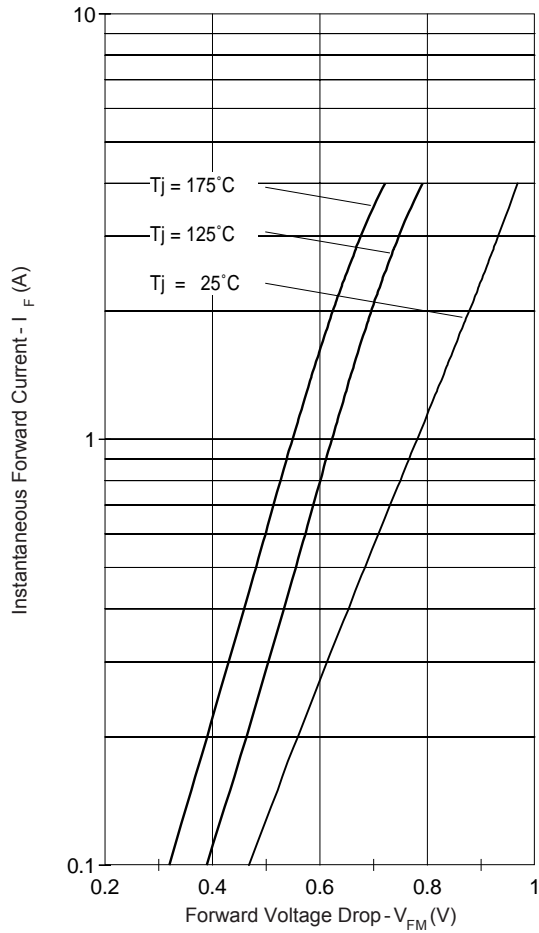


Fig. 1 - Maximum Forward Voltage Drop Characteristics

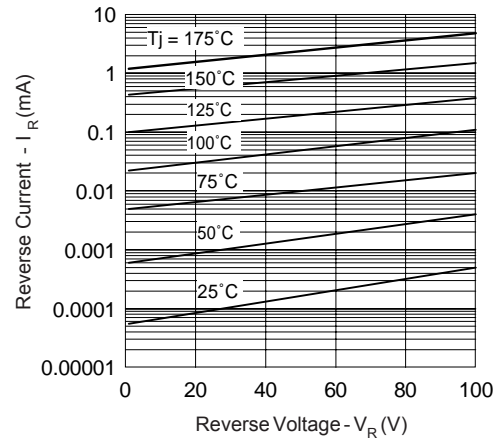


Fig. 2 - Typical Peak Reverse Current Vs. Reverse Voltage

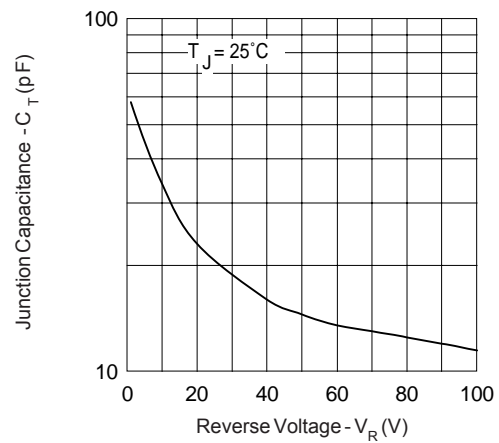


Fig. 3 - Typical Junction Capacitance Vs. Reverse Voltage

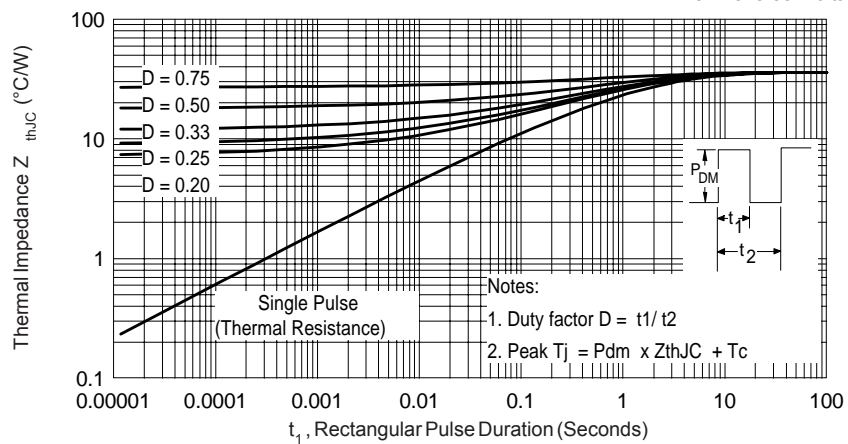


Fig. 4 - Max. Thermal Impedance  $Z_{thJC}$  Characteristics (Per Leg)

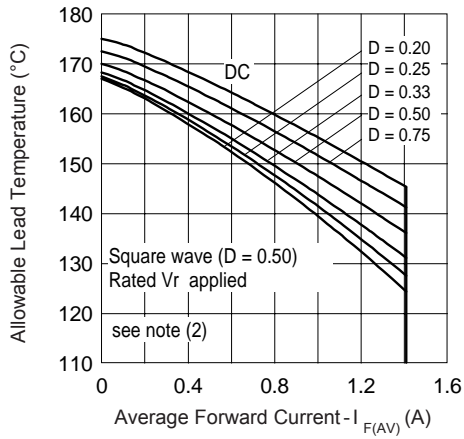


Fig. 4 - Maximum Average Forward Current Vs. Allowable Lead Temperature

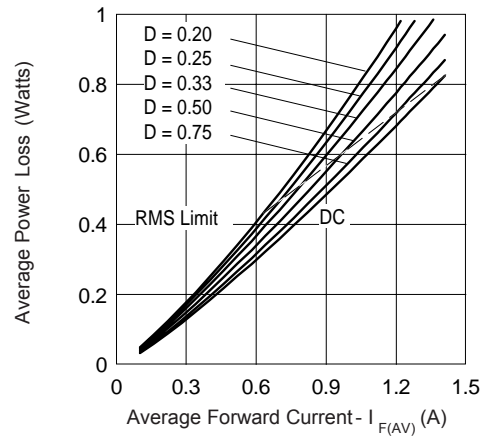


Fig. 5 - Maximum Average Forward Dissipation Vs. Average Forward Current

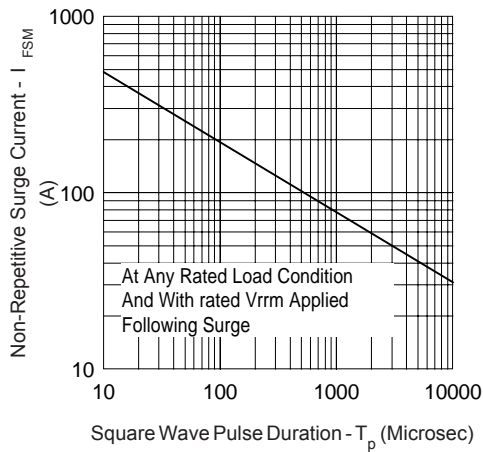


Fig. 6 - Maximum Peak Surge Forward Current Vs. Pulse Duration

(2) Formula used:  $T_c = T_j - (Pd + Pd_{REV}) \times R_{thJC}$ ;

$Pd = \text{Forward Power Loss} = I_{F(AV)} \times V_{FM} @ (I_{F(AV)} / D)$  (see Fig. 6);

$Pd_{REV} = \text{Inverse Power Loss} = V_{R1} \times I_R (1 - D)$ ;  $I_R @ V_{R1} = 80\% \text{ rated } V_R$



Outline Table

